

Fig. 1A

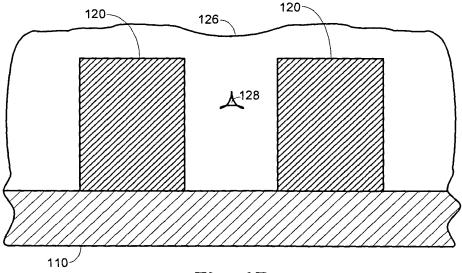


Fig. 1B

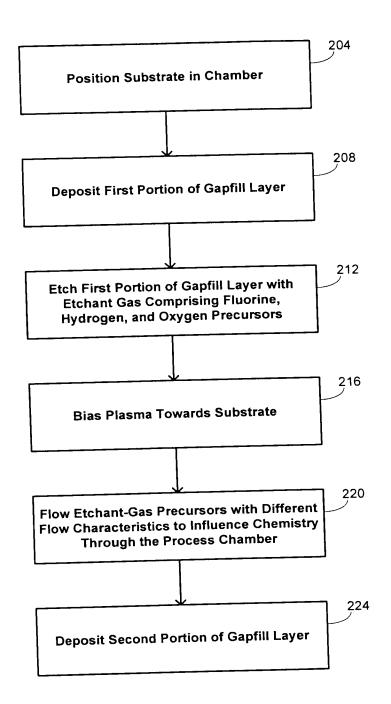


Fig. 2A

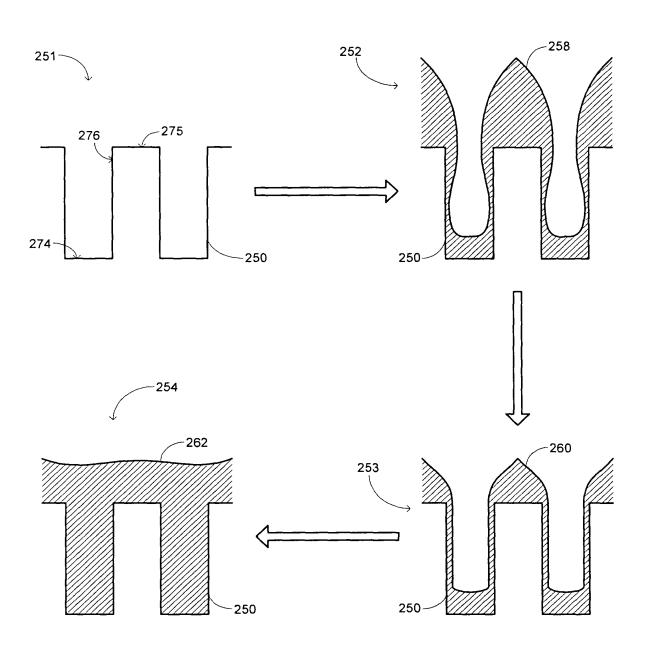
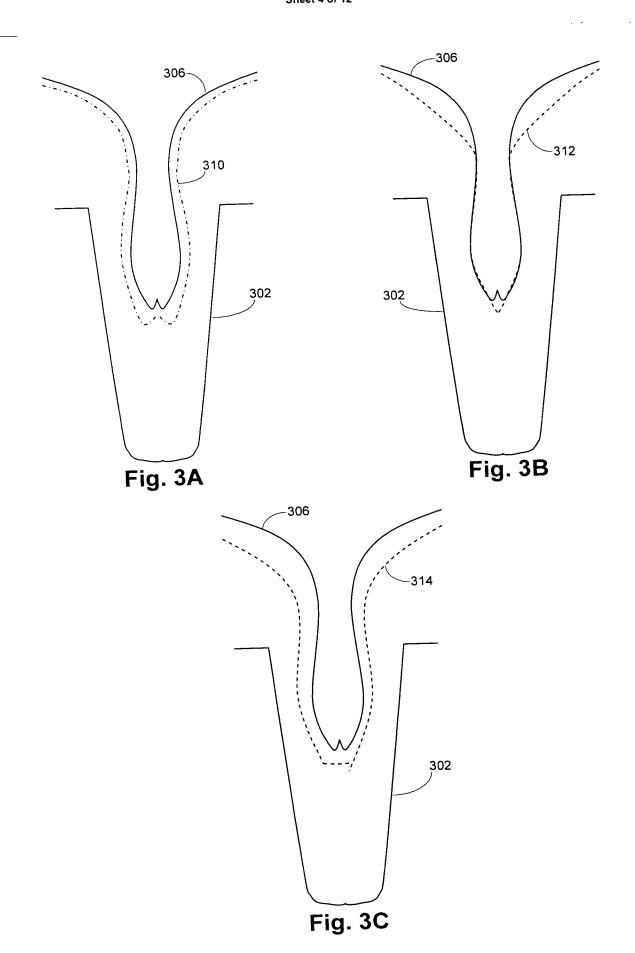
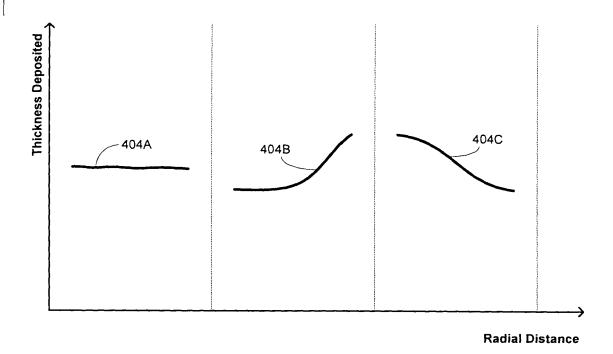


Fig. 2B

Atty. Docket No.: A8067/T51700
Applicant: Hemant P. Mungekar et al.
Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE
FEATURE TOPOGRAPHY MODIFICATION
Sheet 4 of 12



Atty. Docket No.: A8067/T51700
Applicant: Hemant P. Mungekar et al.
Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE
FEATURE TOPOGRAPHY MODIFICATION
Sheet 5 of 12



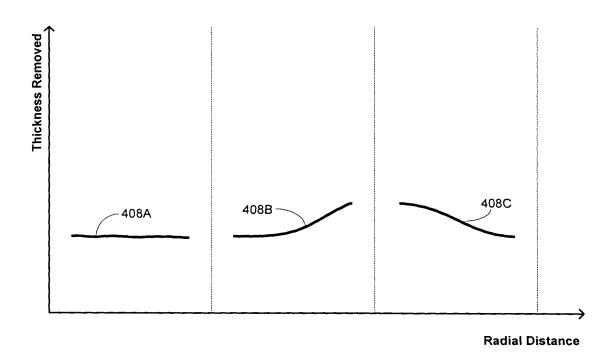
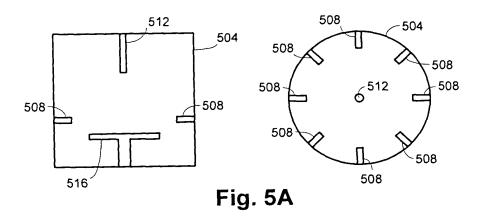
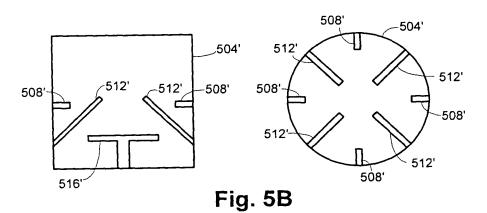
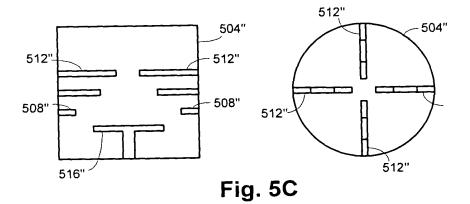


Fig. 4

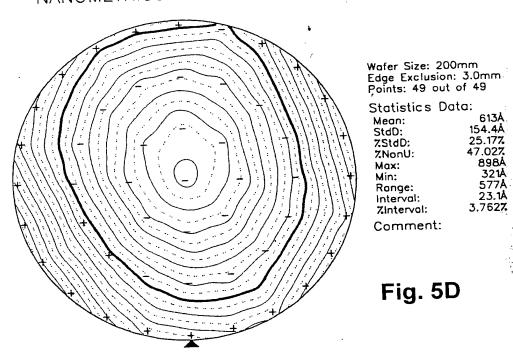




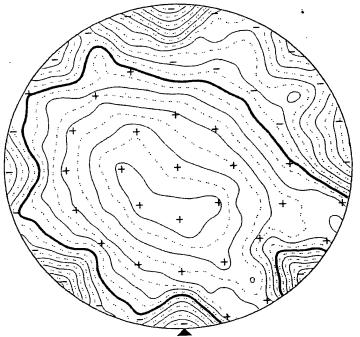


## Atty. Docket No.: A8067/T51700 Applicant: Hemant P. Mungekar et al. Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE FEATURE TOPOGRAPHY MODIFICATION Sheet 7 of 12

## NANOMETRICS 2D CONTOUR MAP



## NANOMETRICS 2D CONTOUR MAP



Wafer Size: 200mm Edge Exclusion: 3.0mm Points: 49 out of 49

## Statistics Data: Mean: 488Å StdD: 46.3Å

 StdD:
 46.3Å

 ZStdD:
 9.48Z

 ZNonU:
 20.67Z

 Max:
 561Å

 Min:
 359Å

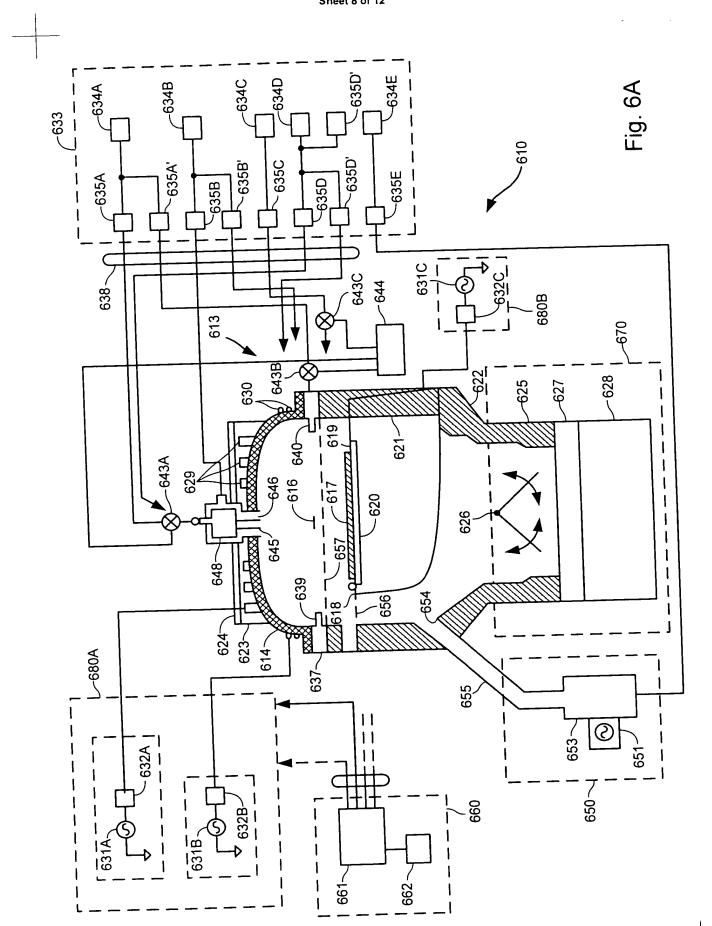
 Range:
 202Å

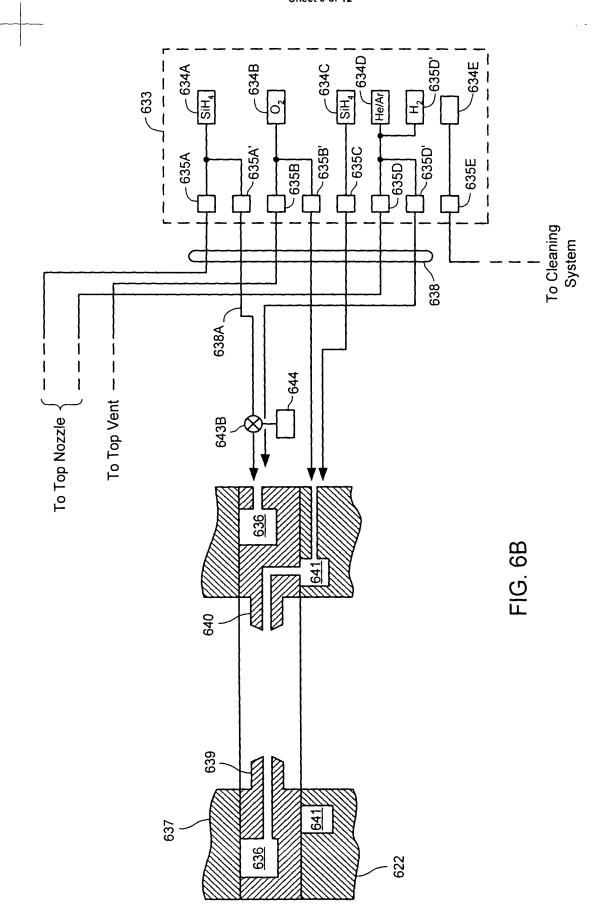
 Interval:
 8.1Å

 Zinterval:
 1.654Z

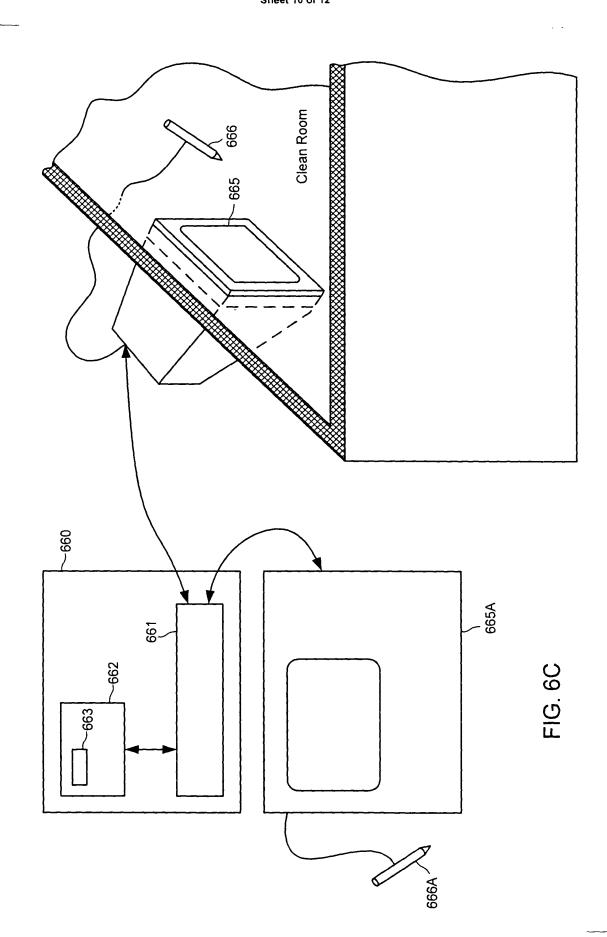
Comment: #7

Fig. 5E





Atty. Docket No.: A8067/T51700
Applicant: Hemant P. Mungekar et al.
Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE
FEATURE TOPOGRAPHY MODIFICATION
Sheet 10 of 12



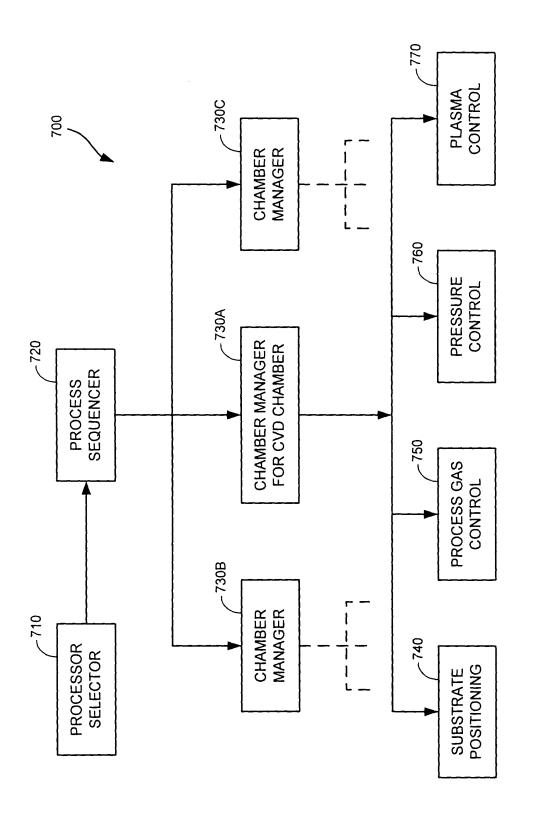


FIG. 6D

